

# Francesco Montalenti

## List of Publications by Year in descending order

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152  
papers

4,208  
citations

147566

31  
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133063

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153  
all docs

153  
docs citations

153  
times ranked

3128  
citing authors

#	ARTICLE	IF	CITATIONS
1	Extending the Time Scale in Atomistic Simulation of Materials. Annual Review of Materials Research, 2002, 32, 321-346.	4.3	614
2	Crossover among structural motifs in transition and noble-metal clusters. Journal of Chemical Physics, 2002, 116, 3856-3863.	1.2	431
3	Jumps and concerted moves in Cu, Ag, and Au(110) adatom self-diffusion. Physical Review B, 1999, 59, 5881-5891.	1.1	131
4	Atomic-Scale Pathway of the Pyramid-to-Dome Transition during Ge Growth on Si(001). Physical Review Letters, 2004, 93, 216102.	2.9	112
5	Structure and Mobility of Defects Formed from Collision Cascades in MgO. Physical Review Letters, 2004, 92, 115505.	2.9	96
6	Delayed Plastic Relaxation on Patterned Si Substrates: Coherent SiGe Pyramids with Dominant{111}Facets. Physical Review Letters, 2007, 98, .	2.9	96
7	Key role of the wetting layer in revealing the hidden path of Ge/Si(001) Stranski-Krastanow growth onset. Physical Review B, 2009, 80, .	1.1	96
8	Leapfrog Diffusion Mechanism for One-Dimensional Chains on Missing-Row Reconstructed Surfaces. Physical Review Letters, 1999, 82, 1498-1501.	2.9	90
9	Monolithic Growth of Ultrathin Ge Nanowires on Si(001). Physical Review Letters, 2012, 109, 085502.	2.9	87
10	Enhanced Relaxation and Intermixing in Ge Islands Grown on Pit-Patterned Si(001) Substrates. Physical Review Letters, 2009, 102, 025502.	2.9	80
11	Closing the Gap between Experiment and Theory: Crystal Growth by Temperature Accelerated Dynamics. Physical Review Letters, 2001, 87, 126101.	2.9	74
12	Cell cycle effects of gemcitabine. International Journal of Cancer, 2001, 93, 401-408.	2.3	73
13	Electronic and elastic contributions in the enhanced stability of Ge() under compressive strain. Surface Science, 2004, 556, 121-128.	0.8	73
14	Faceting of Equilibrium and Metastable Nanostructures: A Phase-Field Model of Surface Diffusion Tackling Realistic Shapes. Crystal Growth and Design, 2015, 15, 2787-2794.	1.4	69
15	Modeling the plastic relaxation onset in realistic SiGe islands on Si(001). Physical Review B, 2008, 78, .	1.1	58
16	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning. Advanced Materials, 2013, 25, 4408-4412.	11.1	55
17	Exploiting past visits or minimum-barrier knowledge to gain further boost in the temperature-accelerated dynamics method. Journal of Chemical Physics, 2002, 116, 4819.	1.2	54
18	Critical Shape and Size for Dislocation Nucleation in $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"> \langle mml:msub \rangle \langle mml:mi \rangle Si \langle /mml:mi \rangle \langle mml:mrow \rangle \langle mml:mn \rangle 1 \langle /mml:mn \rangle \langle mml:mo \rangle \hat{\wedge} \langle /mml:mo \rangle \langle mml:mi \rangle X \langle /mml:mi \rangle$ on Si(001). Physical Review Letters, 2007, 99, 235505.	2.9	54

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19	Simulation of growth of Cu on Ag(001) at experimental deposition rates. Physical Review B, 2002, 66, .	1.1	51
20	Competing mechanisms in adatom diffusion on a channeled surface: Jumps versus metastable walks. Physical Review B, 1998, 58, 3617-3620.	1.1	50
21	Self-Ordering of a Ge Island Single Layer Induced by Si Overgrowth. Physical Review Letters, 2006, 96, 106102.	2.9	42
22	Simulating cancer-cell kinetics after drug treatment: Application to cisplatin on ovarian carcinoma. Physical Review E, 1998, 57, 5877-5887.	0.8	41
23	Measuring the complexity of cell cycle arrest and killing of drugs: Kinetics of phase-specific effects induced by Taxol. , 1999, 37, 113-124.		41
24	Normal-incidence steering effect in crystal growth: Ag/Ag(100). Physical Review B, 2001, 64, .	1.1	41
25	How pit facet inclination drives heteroepitaxial island positioning on patterned substrates. Physical Review B, 2011, 84, .	1.1	41
26	Formation of Ge Nanoripples on Vicinal Si (1110): From Stranski-Krastanow Seeds to a Perfectly Faceted Wetting Layer. Physical Review Letters, 2012, 108, 055503.	2.9	39
27	Highly Mismatched, Dislocation-Free SiGe/Si Heterostructures. Advanced Materials, 2016, 28, 884-888.	11.1	37
28	Strain-induced ordering of small Ge islands in clusters at the surface of multilayered Si-Ge nanostructures. Applied Physics Letters, 2005, 87, 261919.	1.5	36
29	Anomalous Smoothing Preceding Island Formation During Growth on Patterned Substrates. Physical Review Letters, 2012, 109, 156101.	2.9	34
30	Temperature-Dependent Stability of Polytypes and Stacking Faults in $\text{SiC}$ : Reconciling Theory and Experiments. Physical Review Applied, 2019, 12, .	1.5	33
31	Fully coherent growth of Ge on free-standing Si(001) nanomesas. Physical Review B, 2014, 89, .	1.1	32
32	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. ACS Applied Materials & Interfaces, 2016, 8, 2017-2026.	4.0	32
33	Intermixing in heteroepitaxial islands: fast, self-consistent calculation of the concentration profile minimizing the elastic energy. New Journal of Physics, 2008, 10, 083039.	1.2	31
34	Growth kinetics and morphological analysis of homoepitaxial GaAs fins by theory and experiment. Physical Review Materials, 2018, 2, .	0.9	31
35	Imaging Structure and Composition Homogeneity of 300 mm SiGe Virtual Substrates for Advanced CMOS Applications by Scanning X-ray Diffraction Microscopy. ACS Applied Materials & Interfaces, 2015, 7, 9031-9037.	4.0	30
36	Morphological Evolution of Pit-Patterned Si(001) Substrates Driven by Surface-Energy Reduction. Nanoscale Research Letters, 2017, 12, 554.	3.1	30

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37	Collective Shape Oscillations of SiGe Islands on Pit-Patterned Si(001) Substrates: A Coherent-Growth Strategy Enabled by Self-Regulated Intermixing. <i>Physical Review Letters</i> , 2010, 105, 166102.	2.9	29
38	Stability of Ge on Si (1 1 10) surfaces and the role of dimer tilting. <i>Physical Review B</i> , 2012, 85, .	1.1	25
39	Dimers diffusion on (110) (1 $\bar{1}$ -2) metal surfaces. <i>Surface Science</i> , 1999, 432, 27-36.	0.8	24
40	Engineered Coalescence by Annealing 3D Ge Microstructures into High-Quality Suspended Layers on Si. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 19219-19225.	4.0	24
41	Fine control of plastic and elastic relaxation in Ge/Si vertical heterostructures. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	23
42	Competition Between Kinetics and Thermodynamics During the Growth of Faceted Crystal by Phase Field Modeling. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1800518.	0.7	23
43	Fast isotropic adatom diffusion on Ge(105) dot facets. <i>Physical Review B</i> , 2004, 70, .	1.1	21
44	First principles study of Ge $\hat{\wedge}$ Si exchange mechanisms at the Si(001) surface. <i>Applied Physics Letters</i> , 2008, 92, 191908.	1.5	21
45	Aspect-ratio-dependent driving force for nonuniform alloying in Stranski-Krastanow islands. <i>Physical Review B</i> , 2009, 80, .	1.1	21
46	Applying Accelerated Molecular Dynamics to Crystal Growth. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 226, 21-27.	0.7	20
47	Atomistic modeling of step formation and step bunching at the Ge(105) surface. <i>Surface Science</i> , 2005, 591, 23-31.	0.8	20
48	Assessing the delay of plastic relaxation onset in SiGe islands grown on pit-patterned Si(001) substrates. <i>Applied Physics Letters</i> , 2011, 99, 033106.	1.5	20
49	Self-organized evolution of Ge/Si(001) into intersecting bundles of horizontal nanowires during annealing. <i>Applied Physics Letters</i> , 2013, 103, 083109.	1.5	20
50	InAs/GaAs Sharply Defined Axial Heterostructures in Self-Assisted Nanowires. <i>Nano Letters</i> , 2015, 15, 3677-3683.	4.5	20
51	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. <i>Physical Review Materials</i> , 2020, 4, .	0.9	20
52	Spontaneous atomic shuffle in flat terraces: $\hat{\wedge}$ Ag(100). <i>Physical Review B</i> , 2002, 66, .	1.1	19
53	Self-assembled GaAs islands on Si by droplet epitaxy. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	19
54	One-dimensional Ge nanostructures on Si(001) and Si(1 1 10): Dominant role of surface energy. <i>Comptes Rendus Physique</i> , 2013, 14, 542-552.	0.3	19

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55	Ab initio results for the adiabatic atom-surface interaction for helium and neon on a simple metal. <i>Surface Science</i> , 1996, 364, L595-L599.	0.8	18
56	Long jumps in the strong-collision model. <i>Physical Review E</i> , 2000, 61, 6344-6350.	0.8	18
57	Accurate and analytical strain mapping at the surface of Ge/Si(001) islands by an improved flat-island approximation. <i>Surface Science</i> , 2006, 600, 4777-4784.	0.8	18
58	Vertical and lateral ordering of Ge islands grown on Si(001): theory and experiments. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 225001.	0.7	18
59	Quantitative estimate of H abstraction by thermal SiH <sub>3</sub> on hydrogenated Si(001)(2Å-1). <i>Physical Review B</i> , 2007, 75, .	1.1	18
60	Local uniaxial tensile strain in germanium of up to 4% induced by SiGe epitaxial nanostructures. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	18
61	Phase-field simulations of faceted Ge/Si-crystal arrays, merging into a suspended film. <i>Applied Surface Science</i> , 2017, 391, 33-38.	3.1	18
62	Dislocation-Free SiGe/Si Heterostructures. <i>Crystals</i> , 2018, 8, 257.	1.0	18
63	Temperature-dependent evolution of the wetting layer thickness during Ge deposition on Si(001). <i>Nanotechnology</i> , 2011, 22, 285704.	1.3	17
64	Kinetic Control of Morphology and Composition in Ge/GeSn Core/Shell Nanowires. <i>ACS Nano</i> , 2020, 14, 2445-2455.	7.3	17
65	Formation of strain-induced Si-rich and Ge-rich nanowires at misfit dislocations in SiGe: A model supported by photoluminescence data. <i>Applied Physics Letters</i> , 2004, 84, 2895-2897.	1.5	16
66	Stability of shuffle and glide dislocation segments with increasing misfit in Ge <sup>1-x</sup> Si <sup>x</sup> (001) epitaxial layers. <i>Applied Physics Letters</i> , 2005, 86, 041912.	1.5	16
67	Thermal-Hydrogen Promoted Selective Desorption and Enhanced Mobility of Adsorbed Radicals in Silicon Film Growth. <i>Physical Review Letters</i> , 2008, 100, 046105.	2.9	16
68	Crystallinity and microstructure in Si films grown by plasma-enhanced chemical vapor deposition: A simple atomic-scale model validated by experiments. <i>Applied Physics Letters</i> , 2009, 94, 051904.	1.5	16
69	Dynamics of pit filling in heteroepitaxy via phase-field simulations. <i>Physical Review B</i> , 2016, 94, .	1.1	16
70	Modeling the competition between elastic and plastic relaxation in semiconductor heteroepitaxy: From cyclic growth to flat films. <i>Physical Review B</i> , 2016, 94, .	1.1	16
71	Molecular dynamics simulations of extended defects and their evolution in 3C-SiC by different potentials. <i>Modelling and Simulation in Materials Science and Engineering</i> , 2020, 28, 015002.	0.8	15
72	The origin and nature of killer defects in 3C-SiC for power electronic applications by a multiscale atomistic approach. <i>Journal of Materials Chemistry C</i> , 2020, 8, 8380-8392.	2.7	15

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73	Straining Ge bulk and nanomembranes for optoelectronic applications: a systematic numerical analysis. Semiconductor Science and Technology, 2014, 29, 095012.	1.0	15
74	<i>Ab initio</i> study of the diffusion and decomposition pathways of $\text{SiH}_x$ on Si(100). Physical Review B, 2009, 79, .	1.1	14
75	Onset of vertical threading dislocations in Si $_{1-x}$ Ge $_x$ /Si (001) at a critical Ge concentration. APL Materials, 2013, 1, .	2.2	14
76	Continuum modelling of semiconductor heteroepitaxy: an applied perspective. Advances in Physics: X, 2016, 1, 331-367.	1.5	14
77	An MD study of adatom self-diffusion on Au(110) surfaces. Surface Science, 1999, 433-435, 445-448.	0.8	13
78	Diffusion and stability of small vacancy clusters on Cu(100) – a simulation study. Surface Science, 2004, 565, 289-299.	0.8	13
79	Understanding the elastic relaxation mechanisms of strain in Ge islands on pit-patterned Si(001) substrates. Journal of Physics Condensed Matter, 2008, 20, 454217.	0.7	13
80	Hydrostatic strain enhancement in laterally confined SiGe nanostripes. Physical Review B, 2013, 88, .	1.1	13
81	Onset of plastic relaxation in the growth of Ge on Si(001) at low temperatures: Atomic-scale microscopy and dislocation modeling. Physical Review B, 2013, 88, .	1.1	13
82	Optimal Growth Conditions for Selective Ge Islands Positioning on Pit-Patterned Si(001). Nanoscale Research Letters, 2010, 5, 1873-1877.	3.1	12
83	Misfit dislocation gettering by substrate pit-patterning in SiGe films on Si(001). Applied Physics Letters, 2012, 101, .	1.5	12
84	A fast computational method for determining equilibrium concentration profiles in intermixed nanoislands. Journal of Physics Condensed Matter, 2009, 21, 084217.	0.7	11
85	Temperature-controlled coalescence during the growth of Ge crystals on deeply patterned Si substrates. Journal of Crystal Growth, 2016, 440, 86-95.	0.7	11
86	Detailed Analysis of the Shape-dependent Deformation Field in 3D Ge Islands. , 2008, , 421-438.		11
87	Multiscale modeling of island nucleation and growth during Cu(100) homoepitaxy. Physical Review B, 2006, 73, .	1.1	10
88	Assessing the composition of hetero-epitaxial islands via morphological analysis: an analytical model matching GeSi/Si(001) data. Journal of Physics Condensed Matter, 2012, 24, 104018.	0.7	10
89	Reduced-Pressure Chemical Vapor Deposition Growth of Isolated Ge Crystals and Suspended Layers on Micrometric Si Pillars. ACS Applied Materials & Interfaces, 2016, 8, 26374-26380.	4.0	10
90	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. Nanotechnology, 2017, 28, 485303.	1.3	10

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91	Ab-initio adiabatic noble gas-metal interaction: the role of the induced polarization charge. <i>Surface Science</i> , 1998, 401, L383-L387.	0.8	9
92	Long-jump probabilities in a BGK model for surface diffusion. <i>Chemical Physics Letters</i> , 1999, 315, 153-157.	1.2	9
93	Transition-path spectra at metal surfaces. <i>Surface Science</i> , 2003, 543, 141-152.	0.8	9
94	Atomic-scale modeling of next-layer nucleation and step flow at the Ge(105) rebonded-step surface. <i>Physical Review B</i> , 2007, 75, .	1.1	9
95	Dislocation engineering in SiGe heteroepitaxial films on patterned Si (001) substrates. <i>Applied Physics Letters</i> , 2011, 98, 121908.	1.5	9
96	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. <i>Materials</i> , 2019, 12, 3223.	1.3	9
97	Universal law for piecewise dimer diffusion. <i>Physical Review B</i> , 1999, 60, 11102-11109.	1.1	8
98	A multiscale model of the plasma assisted deposition of crystalline silicon. <i>Surface and Coatings Technology</i> , 2007, 201, 8863-8867.	2.2	8
99	Strain and strain-release engineering at epitaxial SiGe islands on Si(001) for microelectronic applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 90-94.	1.7	8
100	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 117-122.	1.9	8
101	Misfit-Dislocation Distributions in Heteroepitaxy: From Mesoscale Measurements to Individual Defects and Back. <i>Physical Review Applied</i> , 2018, 10, .	1.5	8
102	Dynamics of crosshatch patterns in heteroepitaxy. <i>Physical Review B</i> , 2019, 100, .	1.1	8
103	Selective Area Epitaxy of GaAs/Ge/Si Nanomembranes: A Morphological Study. <i>Crystals</i> , 2020, 10, 57.	1.0	8
104	Mobility of atomic chains on channeled surfaces. <i>Journal of Chemical Physics</i> , 2000, 113, 349-356.	1.2	7
105	Atomistic simulation of a 60° shuffle dislocation segment migrating in a Ge/SiGe(001) epitaxial film. <i>Journal of Physics Condensed Matter</i> , 2005, 17, 7505-7515.	0.7	7
106	Binding sites for SiH <sub>2</sub> /Si(001): A combined ab initio, tight-binding, and classical investigation. <i>Surface Science</i> , 2006, 600, 4445-4453.	0.8	7
107	From plastic to elastic stress relaxation in highly mismatched SiGe/Si heterostructures. <i>Acta Materialia</i> , 2016, 114, 97-105.	3.8	7
108	Structure and Stability of Partial Dislocation Complexes in 3C-SiC by Molecular Dynamics Simulations. <i>Materials</i> , 2019, 12, 3027.	1.3	7

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109	Relaxed SiGe heteroepitaxy on Si with very thin buffer layers: experimental LEPECVD indications and an interpretation based on strain-dependent dislocation nature. <i>Microelectronic Engineering</i> , 2004, 76, 290-296.	1.1	6
110	Impact-driven effects in thin-film growth: steering and transient mobility at the Ag(110) surface. <i>Nanotechnology</i> , 2006, 17, 3556-3562.	1.3	6
111	Si/Ge exchange mechanisms at the Ge(105) surface. <i>Physical Review B</i> , 2010, 81, .	1.1	6
112	Sunburst pattern by kinetic segregation in core-shell nanowires: A phase-field study. <i>Applied Surface Science</i> , 2020, 517, 146056.	3.1	6
113	Controlling the relaxation mechanism of low strain Si <sup>x</sup> /Ge <sup>x</sup> /Si(001) layers and reducing the threading dislocation density by providing a preexisting dislocation source. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	6
114	Diffusion of one-dimensional clusters on Au and Pt(110) ( $1\text{\AA}-2$ ). <i>Surface Science</i> , 2000, 454-456, 575-578.	0.8	5
115	Leapfrog-induced selective faceting in the growth of missing-row (110) surfaces. <i>Chemical Physics Letters</i> , 2004, 398, 50-55.	1.2	5
116	Interaction of SiH <sub>x</sub> precursors with hydrogen-covered Si surfaces: Impact dynamics and adsorption sites. <i>Surface Science</i> , 2007, 601, 3970-3973.	0.8	5
117	Self-Ordering of Misfit Dislocation Segments in Epitaxial SiGe Islands on Si(001). <i>Journal of Applied Physics</i> , 2011, 110, 044310.	1.1	5
118	Alignment control of self-ordered three dimensional SiGe nanodots. <i>Semiconductor Science and Technology</i> , 2018, 33, 114014.	1.0	5
119	Nature and Shape of Stacking Faults in 3C-SiC by Molecular Dynamics Simulations. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000598.	0.7	5
120	Three-dimensional SiGe/Si heterostructures: Switching the dislocation sign by substrate under-etching. <i>Physical Review Materials</i> , 2017, 1, .	0.9	5
121	Probability of dimer reassociation in two dimensions. <i>Physical Review E</i> , 2000, 61, 3411-3416.	0.8	4
122	Structure, interface abruptness and strain relaxation in self-assisted grown InAs/GaAs nanowires. <i>Applied Surface Science</i> , 2017, 395, 29-36.	3.1	4
123	Faceting of Si and Ge crystals grown on deeply patterned Si substrates in the kinetic regime: phase-field modelling and experiments. <i>Scientific Reports</i> , 2021, 11, 18825.	1.6	4
124	Atomic-scale insights on the formation of ordered arrays of edge dislocations in Ge/Si(001) films via molecular dynamics simulations. <i>Scientific Reports</i> , 2022, 12, 3235.	1.6	4
125	Machine learning potential for interacting dislocations in the presence of free surfaces. <i>Scientific Reports</i> , 2022, 12, 3760.	1.6	4
126	Theoretical evidence for fast H-divacancy rotation on H/Pd(111). <i>Chemical Physics Letters</i> , 2004, 400, 163-168.	1.2	3



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127	Modeling the evolution of germanium islands on silicon(001) thin films. , 2011, , 211-246.		3
128	Enhancing elastic stress relaxation in SiGe/Si heterostructures by Si pillar necking. Applied Physics Letters, 2016, 109, 182112.	1.5	3
129	Computational Analysis of Low-Energy Dislocation Configurations in Graded Layers. Crystals, 2020, 10, 661.	1.0	3
130	Thermodynamic driving force in the formation of hexagonal-diamond Si and Ge nanowires. Applied Surface Science, 2021, 545, 148948.	3.1	3
131	Stress-Induced Acceleration and Ordering in Solid-State Dewetting. Physical Review Letters, 2022, 128, 026101.	2.9	3
132	Charge transfer in chemisorption: N and Si on Al. Solid State Communications, 1996, 99, 7-11.	0.9	2
133	Atomistic approach for Boron Transient Enhanced Diffusion and clustering. , 2008, , .		2
134	Strained MOSFETs on ordered SiGe dots. Solid-State Electronics, 2011, 65-66, 81-87.	0.8	2
135	Density functional study of the decomposition pathways of SiH <sub>3</sub> and GeH <sub>3</sub> at the Si(100) and Ge(100) surfaces. Journal of Physics Condensed Matter, 2012, 24, 104002.	0.7	2
136	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning (Adv. Mater. 32/2013). Advanced Materials, 2013, 25, 4407-4407.	11.1	2
137	Fully coherent Ge islands growth on Si nano-pillars by selective epitaxy. Materials Science in Semiconductor Processing, 2017, 70, 30-37.	1.9	2
138	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. Nanomaterials, 2020, 10, 1512.	1.9	2
139	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. Crystal Growth and Design, 2020, 20, 2914-2920.	1.4	2
140	Delayed plastic relaxation limit in SiGe islands grown by Ge diffusion from a local source. Journal of Applied Physics, 2015, 117, 104309.	1.1	1
141	Anisotropic extended misfit dislocations in overcritical SiGe films by local substrate patterning. Nanotechnology, 2016, 27, 425301.	1.3	1
142	Elastic and Plastic Stress Relaxation in Highly Mismatched SiGe/Si Crystals. MRS Advances, 2016, 1, 3403-3408.	0.5	1
143	Motion of crystalline inclusions by interface diffusion in the proximity of free surfaces. Journal of Nanoparticle Research, 2019, 21, 1.	0.8	1
144	Prismatic Ge-rich inclusions in the hexagonal SiGe shell of GaP@Si@SiGe nanowires by controlled faceting. Nanoscale, 2021, 13, 9436-9445.	2.8	1

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145	Phase-field modeling of the morphological evolution of ringlike structures during growth: Thermodynamics, kinetics, and template effects. <i>Physical Review Materials</i> , 2022, 6, .	0.9	1
146	Comment on "Scaling behavior of one-dimensional Pt chains migration on Pt(110)-(1 $\times$ 2) surface". <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2000, 277, 185-187.	0.9	0
147	Spontaneous Ge island ordering promoted by partial silicon capping. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 823-827.	1.9	0
148	CONCENTRATION PROFILES IN HETEROEPITAXIAL NANOISLANDS. , 2009, , .		0
149	Phenomenological model of nanocrystalline silicon film formation by plasma-enhanced chemical vapor deposition. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2009, 45, 322-327.	0.2	0
150	Si CMOS compatible, compliant integration of lattice-mismatched semiconductors on Si(001): Example of fully coherent Ge/Si nanostructures. , 2014, , .		0
151	Slip trace-induced terrace erosion. <i>Applied Surface Science</i> , 2019, 466, 454-458.	3.1	0
152	Diffusion of Adatoms and Small Clusters on Missing-Row-Reconstructed Surfaces. <i>NATO Science Series Series II, Mathematics, Physics and Chemistry</i> , 2001, , 237-245.	0.1	0